

# GP1S36J0000F

**Phototransistor Output, Transmissive Photointerrupter** with Tilt Direction (3-direction) **Detecting** 

## **■** Description

GP1S36J0000F is a compact-package, phototransistor output, transmissive photointerrupter, with opposing emitter and detector in a molding that provides noncontact sensing.

This is a 2-phase output device, suitable for detection of the position (3 direction).

#### ■ Features

- 1. Transmissive with phototransistor output
- 2. Highlights:
  - Built-in a ball (2 phase output)
  - Compact
  - PWB mounting type
  - 3-direction detection
- 3. Lead free and RoHS directive compliant

## ■Agency approvals/Compliance

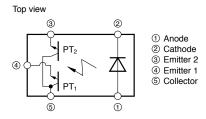
1. Compliant with RoHS directive

## ■ Applications

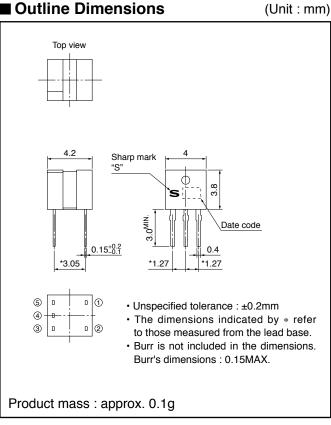
- 1. General purpose detection of device direction.
- 2. Example: Camera, DSC, Camcorder, Robot



# **■ Internal Connection Diagram**



## **■** Outline Dimensions



Plating material: SnCu (Cu: TYP. 2%)



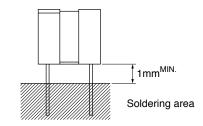
Date code (2 digit)						
1st o	digit	2nd digit				
Year of p	Year of production		production			
A.D.	Mark	Month	Mark			
2000	0	1	1			
2001	1	2	2			
2002	2	3	3			
2003	3	4	4			
2004	4	5	5			
2005	5	6	6			
2006	6	7	7			
2007	7	8	8			
2008	8	9	9			
2009	9	10	X			
2010	0	11	Y			
:	:	12	Z			

repeats in a 10 year cycle

Country of origin Japan, China



$lacktriangle$ Absolute Maximum Ratings $(T_a=25^\circ)$							
	Parameter	Symbol	Rating	Unit			
	Forward current	$I_{F}$	50	mA			
Input	Reverse voltage	$V_R$	6	V			
	Power dissipation	P	75	mW			
	Collector-emitter voltage	$V_{CE1O}$ $V_{CE2O}$	35	V			
Output	Emitter-collector voltage	V <sub>E1CO</sub>	6	V			
	Collector current	$I_{C}$	20	mA			
	Collector power dissipation	P <sub>C</sub>	75	mW			
Total power dissipation		P <sub>tot</sub>	100	mW			
Operating temperature		Topr	-25 to +85	°C			
Storage temperature		T <sub>stg</sub>	-40 to +100	°C			
*1Soldering temperature 1		T <sub>sol</sub>	260	°C			
*2Solder	ring temperature 2	T <sub>sol</sub>	320	°C			



# **■** Electro-optical Characteristics

 $(T_a=25^{\circ}C)$ 

Parameter		Symbol	Condition	MIN.	TYP.	MAX.	Unit	
Forward voltage		$V_F$ $I_F=20mA$		_	1.2	1.4	V	
прис	Input Reverse current		$I_R$	$V_R=3V$	_	_	10	μΑ
*3Output	Dark current		$I_{CEO}$	$V_{CE}=20V$	_	_	100	nA
	Collector current		$I_{C}$	$V_{CE}=5V$ , $I_F=5mA$	60	_	350	μΑ
*3Transfer	*4Leak current		I <sub>LEAK</sub>	V <sub>CE</sub> =5V, I <sub>F</sub> =5mA	_	_	15	μΑ
charac-	Collector-emitter saturation voltage		V <sub>CE(sat)</sub>	$I_{F}=10\text{mA}, I_{C}=60\mu\text{A}$	_	-	0.4	V
teristics	teristics $\begin{array}{c} \text{Response time} & \begin{array}{c} \text{Rise time} \\ \end{array} \end{array}$		t <sub>r</sub>	V 5V I 100 A D 11c0	_	50	150	μs
			$t_{\rm f}$	$V_{CE}$ =5V, $I_{C}$ =100 $\mu$ A, $R_{L}$ =1 $k\Omega$	_	50	150	μs

<sup>\*3</sup> Output and coupling characteristics are common to the both phototransistors.

<sup>\*1</sup> For MAX. 5 s (Soldering area is shown below)

<sup>\*2</sup> For MAX. 2 s (Eachterriral shall be hand-soldered at more 0.8mm for from bottom of resin pack-

<sup>\*4</sup> Characteristics except leak current is measured at  $\theta$ =0°,  $\phi$ =0°. Leak current is the output current of transistor when  $\theta$ =±90°,  $\phi$ =0° and I<sub>C</sub>=OFF.

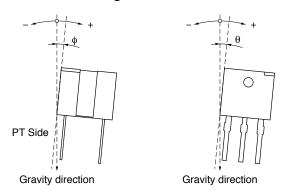


■ Absolute Maximum Ratings						$(I_F=5mA)$	4, V <sub>CC</sub>	=5V,	φ≤±5)		
θ	-90°	\$	_75°	<b>*</b>	-15°	\$	+15°	$\leftrightarrow$	+75°	$\Leftrightarrow$	+90°
$I_{C1}$	ON					Indefinite		OFF			
$I_{C2}$	OFF Indefinite				ON						

$$\begin{split} &I_{C1}: Output \ current \ of \ phototransistors \ PT_1 \\ &I_{C2}: Output \ current \ of \ phototransistors \ PT_2 \\ &\theta: Device \ condition: \ Refer \ to \ the \ next \ figure \\ &\phi: Device \ condition: \ Refer \ to \ the \ next \ figure \\ &ON: Output \ current \ of \ phototransistors: \ 60\mu A \ or \ more \\ &OFF: Output \ current \ of \ phototransistors: \ 15\mu A \ or \ less \end{split}$$

\* Output of ON/OFF is under the condition that the device is in stationary state.

## Device state diagram



# **■** Supplement

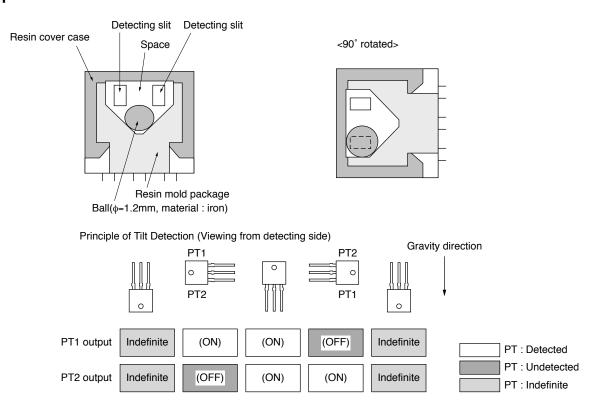




Fig.1 Forward Current vs.

Ambient Temperature

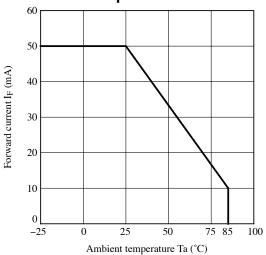


Fig.3 Forward Current vs. Forward Voltage

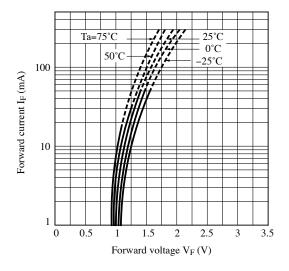


Fig.5 Collector Current vs.
Collector-emitter Voltage

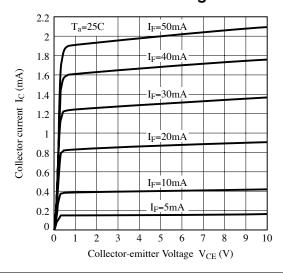


Fig.2 Power Dissipation vs. Ambient Temperature

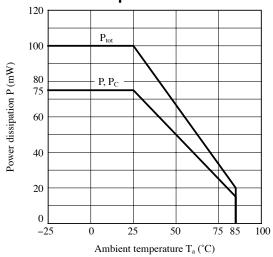


Fig.4 Collector Current vs. Forward Current

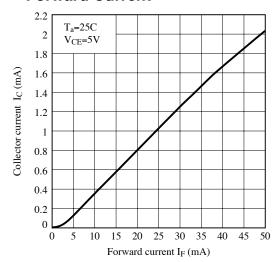


Fig.6 Relative Collector Current vs.
Ambient Temperature

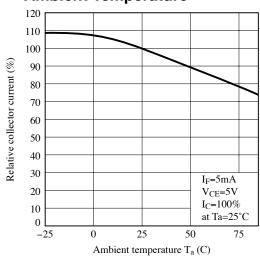




Fig.7 Collector-emitter Saturation Voltage vs.
Ambient Temperature

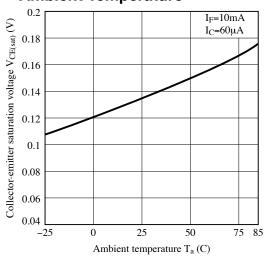


Fig.8 Response Time vs. Load Resistance

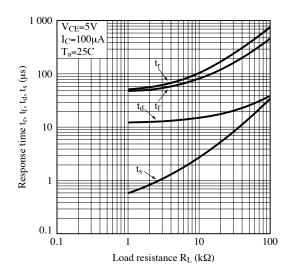


Fig.9 Collector Dark Current vs. Ambient Temperature

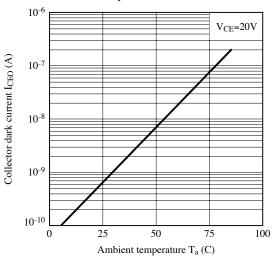
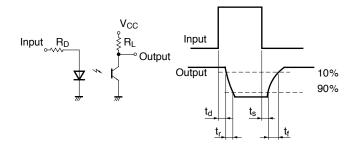


Fig.10 Test Circuit for Response Time



Remarks: Please be aware that all data in the graph are just for reference and not for guarantee.



## ■ Design Considerations

## Design guide

#### 1) Prevention of malfunction

To prevent photointerrupter from faulty operation caused by external light, do not set the detecting face to the external light.

Please confirm that there is no mis-operation by magnetic field in use, for prevention of mis-operation by magnetic field.

Please don't let the device put in change of temperature that makes dew for prevention of mis-operation by dew.

If the device is put in the change of temperature which makes dew, please leave the device for enough time in the constant temperature for use.

This product is not designed against irradiation and incorporates non-coherent IRED.

## Degradation

In general, the emission of the IRED used in photointerrupter will degrade over time.

In the case of long term operation, please take the general IRED degradation (50% degradation over 5 years) into the design consideration.

#### Parts

This product is assembled using the below parts.

#### Photodetector (qty.: 1)

Category	Maximum Sensitivity wavelength (nm)		Sensitivity wavelength (nm)	Response time (µs)	
Phototransistor	Silicon (Si)	800	700 to 1 200	12	

## • Photo emitter (qty.: 1)

Category	Material	Maximum light emitting wavelength (nm)	I/O Frequency (MHz)
Infrared emitting diode (non-coherent)	Gallium arsenide (GaAs)	950	0.3

#### Material

Case	Lead frame	Lead frame plating	Packing case	Metal ball
Black polyphenylene sulfide resin (UL94 V-0)	42Alloy	SnCu plating	Polycarbonate	Fe



## ■ Manufacturing Guidelines

## Soldering Method

#### Flow Soldering:

Soldering should be completed below 260°C and within 5 s.

Please solder within one time.

Soldering area is 1mm or more away from the bottom of housing.

Please take care not to let any external force exert on lead pins.

Please don't do soldering with preheating, and please don't do soldering by reflow.

## Hand soldering

Hand soldering should be completed within 2 s when the point of solder iron is below 320°C.

Soldering area is 0.8mm or more away from the bottom of housing.

Please solder within one time.

Soldered product shall treat at normal temperature.

## Lead pin

Lead terminals of this product are tin copper alloy plated. Before usage, please evaluate solderability with actual conditions and confirm. And the uniformity in color for the lead terminals are not specified.

#### Other notice

Please test the soldering method in actual condition and make sure the soldering works fine, since the impact on the junction between the device and PCB varies depending on the tooling and soldering conditions.

## Cleaning instructions

The device shall not be washed with washing material, for there is possibility to remain washing material in internal space of this transmissive type photointerrupter.

#### Presence of ODC

This product shall not contain the following materials.

And they are not used in the production process for this product.

Regulation substances: CFCs, Halon, Carbon tetrachloride, 1.1.1-Trichloroethane (Methylchloroform)

Specific brominated flame retardants such as the PBBOs and PBBs are not used in this product at all.

This product shall not contain the following materials banned in the RoHS Directive (2002/95/EC).

•Lead, Mercury, Cadmium, Hexavalent chromium, Polybrominated biphenyls (PBB), Polybrominated diphenyl ethers (PBDE).



# ■ Package specification

# ● Sleeve package

# Package materials

Sleeve: Polystyrene

Stopper: Styrene-Butadiene

# Package method

MAX. 40 pcs. of products shall be packaged in a sleeve. Both ends shall be closed by tabbed and tabless stoppers.

MAX. 50 sleeves in one case.



## **■** Important Notices

- The circuit application examples in this publication are provided to explain representative applications of SHARP devices and are not intended to guarantee any circuit design or license any intellectual property rights. SHARP takes no responsibility for any problems related to any intellectual property right of a third party resulting from the use of SHARP's devices.
- · Contact SHARP in order to obtain the latest device specification sheets before using any SHARP device. SHARP reserves the right to make changes in the specifications, characteristics, data, materials, structure, and other contents described herein at any time without notice in order to improve design or reliability. Manufacturing locations are also subject to change without notice.
- · Observe the following points when using any devices in this publication. SHARP takes no responsibility for damage caused by improper use of the devices which does not meet the conditions and absolute maximum ratings to be used specified in the relevant specification sheet nor meet the following conditions:
- (i) The devices in this publication are designed for use in general electronic equipment designs such as:
  - --- Personal computers
  - --- Office automation equipment
  - --- Telecommunication equipment [terminal]
  - --- Test and measurement equipment
  - --- Industrial control
  - --- Audio visual equipment
  - --- Consumer electronics
- (ii) Measures such as fail-safe function and redundant design should be taken to ensure reliability and safety when SHARP devices are used for or in connection

with equipment that requires higher reliability such as:

- --- Transportation control and safety equipment (i.e., aircraft, trains, automobiles, etc.)
- --- Traffic signals
- --- Gas leakage sensor breakers
- --- Alarm equipment
- --- Various safety devices, etc.
- (iii) SHARP devices shall not be used for or in connection with equipment that requires an extremely high level of reliability and safety such as:
  - --- Space applications
  - --- Telecommunication equipment [trunk lines]
  - --- Nuclear power control equipment
  - --- Medical and other life support equipment (e.g., scuba).
- · If the SHARP devices listed in this publication fall within the scope of strategic products described in the Foreign Exchange and Foreign Trade Law of Japan, it is necessary to obtain approval to export such SHARP devices.
- This publication is the proprietary product of SHARP and is copyrighted, with all rights reserved. Under the copyright laws, no part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, for any purpose, in whole or in part, without the express written permission of SHARP. Express written permission is also required before any use of this publication may be made by a third party.
- · Contact and consult with a SHARP representative if there are any questions about the contents of this publication.